

IN THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claim 1 (Currently Amended): A semiconductor device comprising:  
a semiconductor element having an electrode;  
a metal block having a first surface and a second surface opposite to said first surface;  
an electrode terminal joined to said first surface of said metal block; and  
a ceramic substrate joined directly to said second surface of said metal block and  
having metal layers formed on both surfaces,

wherein said semiconductor element and said electrode are joined to said first surface  
of said metal block through a jointing material.

Claim 2 (Original): The semiconductor device according to claim 1, wherein said  
metal layers formed on said both surfaces of said ceramic substrate are the same with each  
other in thickness.

Claim 3 (Currently Amended): The semiconductor device according to claim 1,  
wherein  
said semiconductor element includes a plurality of semiconductor elements;  
said metal block and said ceramic substrate are separated per ~~insulation unit of at least~~  
~~one of said plurality of semiconductor elements~~ insulation unit of at least one of said plurality  
of semiconductor elements;

~~either said metal block or said ceramic substrate is provided to be in corresponding to at least one of said plurality of semiconductor elements; and~~

said metal block is provided to be in correspondence with at least one of said plurality of semiconductor elements; and

~~either said metal block or said ceramic substrate not corresponding to at least one of said plurality of semiconductor elements extends entirely over said insulation unit~~

said ceramic substrate extends over all of said plurality of semiconductor elements for forming said insulation unit.

Claim 4 (Previously Presented): The semiconductor device according to claim 1, wherein said metal block includes a surface having a region larger than a surface of said jointing material on a side opposite to said jointing material, said surface of said jointing material lying on a side opposite to said semiconductor element.

Claim 5 (Original): The semiconductor device according to claim 1, wherein a gap between said metal block and said semiconductor element becomes wider as a distance from a center of said semiconductor element becomes longer; and said gap is filled with said jointing material.

Claim 6 (Original): A semiconductor device comprising:  
a metal block having a first surface and a second surface opposite to said first surface;  
a semiconductor element joined to said first surface of said metal block through a jointing material;

a resin insulating layer having a third surface and a fourth surface opposite to said third surface, said third surface being joined to said second surface of said metal block; and  
a resin package for sealing said metal block and said semiconductor element,  
wherein said fourth surface of said resin insulating layer is exposed, and  
said resin insulating layer has an elasticity higher than that of said resin package.

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Claim 7 (Original): The semiconductor device according to claim 6, wherein said resin insulating layer is made of a silicon resin including a ceramic material for filling said silicon resin.

Claim 8 (Original): The semiconductor device according to claim 6, wherein said metal block is provided per insulation unit of said semiconductor element.

Claim 9 (Previously Presented): The semiconductor device according to claim 6, wherein said metal block includes a surface having a region larger than a surface of said jointing material on a side opposite to said jointing material, said surface of said jointing material lying on a side opposite to said semiconductor element.

Claim 10 (Original): The semiconductor device according to claim 6, wherein  
a gap between said metal block and said semiconductor element becomes wider as a distance from a center of said semiconductor element becomes longer; and  
said gap is filled with said jointing material.

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Claim 11 (New): The semiconductor device according to claim 1, wherein  
said semiconductor element includes a plurality of semiconductor elements;  
said metal block and said ceramic substrate are separated per insulation unit of at least  
one of said plurality of semiconductor elements;  
said ceramic substrate is provided to be in correspondence with at least one of said  
plurality of semiconductor elements; and  
said metal block extends over all of said plurality of semiconductor elements for  
forming said insulation unit.

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